

Jun Suda

List of Publications by Year in descending order

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293
papers

5,089
citations

101543

36
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155660

55
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304
all docs

304
docs citations

304
times ranked

2781
citing authors

#	ARTICLE	IF	CITATIONS
1	Nearly Ideal Current–Voltage Characteristics of Schottky Barrier Diodes Formed on Hydride-Vapor-Phase-Epitaxy-Grown GaN Free-Standing Substrates. <i>Applied Physics Express</i> , 2010, 3, 101003.	2.4	124
2	Lifetime–killing defects in 4H–SiC epilayers and lifetime control by low–energy electron irradiation. <i>Physica Status Solidi (B): Basic Research</i> , 2008, 245, 1327-1336.	1.5	112
3	Ultrahigh-Voltage SiC p-i-n Diodes With Improved Forward Characteristics. <i>IEEE Transactions on Electron Devices</i> , 2015, 62, 374-381.	3.0	110
4	Highly effective activation of Mg-implanted p-type GaN by ultra-high-pressure annealing. <i>Applied Physics Letters</i> , 2019, 115, .	3.3	110
5	Characterization of stacking faults in 4H-SiC epilayers by room-temperature microphotoluminescence mapping. <i>Applied Physics Letters</i> , 2008, 92, 221906.	3.3	101
6	21-kV SiC BJTs With Space-Modulated Junction Termination Extension. <i>IEEE Electron Device Letters</i> , 2012, 33, 1598-1600.	3.9	96
7	Zirconium Diboride (0001) as an Electrically Conductive Lattice-Matched Substrate for Gallium Nitride. <i>Japanese Journal of Applied Physics</i> , 2001, 40, L1280-L1282.	1.5	94
8	The temperature dependence of the refractive indices of GaN and AlN from room temperature up to 515–°C. <i>Journal of Applied Physics</i> , 2008, 104, .	2.5	90
9	Temperature and doping dependencies of electrical properties in Al-doped 4H-SiC epitaxial layers. <i>Journal of Applied Physics</i> , 2009, 106, .	2.5	89
10	Space-Modulated Junction Termination Extension for Ultrahigh-Voltage p-i-n Diodes in 4H-SiC. <i>IEEE Transactions on Electron Devices</i> , 2012, 59, 414-418.	3.0	87
11	Hall-effect measurements of metalorganic vapor-phase epitaxy-grown p-type homoepitaxial GaN layers with various Mg concentrations. <i>Japanese Journal of Applied Physics</i> , 2017, 56, 031001.	1.5	82
12	Design and Fabrication of GaN p-n Junction Diodes With Negative Beveled-Mesa Termination. <i>IEEE Electron Device Letters</i> , 2019, 40, 941-944.	3.9	78
13	Interface Properties of 4H-SiC (<math>\rho_{\text{BT}}</math> Over) in NO. <i>IEEE Transactions on Electron Devices</i> , 2015, 62, 309-315.	3.0	74
14	Simulation and Experimental Study on the Junction Termination Structure for High-Voltage 4H-SiC PiN Diodes. <i>IEEE Transactions on Electron Devices</i> , 2008, 55, 1841-1846.	3.0	73
15	Impacts of recombination at the surface and in the substrate on carrier lifetimes of n-type 4H–SiC epilayers. <i>Journal of Applied Physics</i> , 2010, 108, 083721.	2.5	72
16	4H–SiC MISFETs with nitrogen–containing insulators. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009, 206, 2374-2390.	1.8	70
17	Impact Ionization Coefficients in 4H-SiC Toward Ultrahigh-Voltage Power Devices. <i>IEEE Transactions on Electron Devices</i> , 2015, 62, 3326-3333.	3.0	70
18	Analytical model for reduction of deep levels in SiC by thermal oxidation. <i>Journal of Applied Physics</i> , 2012, 111, .	2.5	69

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19	21.7 kV 4H-SiC PiN Diode with a Space-Modulated Junction Termination Extension. Applied Physics Express, 2012, 5, 064001.	2.4	67
20	Triple Shockley type stacking faults in 4H-SiC epilayers. Applied Physics Letters, 2009, 94, .	3.3	66
21	Effects of Nitridation on 4H-SiC MOSFETs Fabricated on Various Crystal Faces. IEEE Transactions on Electron Devices, 2013, 60, 1260-1262.	3.0	61
22	Characterization of major in-grown stacking faults in 4H-SiC epilayers. Physica B: Condensed Matter, 2009, 404, 4745-4748.	2.7	59
23	Sources of carrier compensation in metalorganic vapor phase epitaxy-grown homoepitaxial n-type GaN layers with various doping concentrations. Applied Physics Express, 2018, 11, 041001.	2.4	59
24	High temperature annealing of n-type 4H-SiC: Impact on intrinsic defects and carrier lifetime. Journal of Applied Physics, 2012, 111, .	2.5	58
25	Investigation on origin of Z1/2 center in SiC by deep level transient spectroscopy and electron paramagnetic resonance. Applied Physics Letters, 2013, 102, .	3.3	56
26	Carrier Recombination in n-Type 4H-SiC Epilayers with Long Carrier Lifetimes. Applied Physics Express, 2012, 5, 101301.	2.4	55
27	Impact ionization coefficients and critical electric field in GaN. Journal of Applied Physics, 2021, 129, .	2.5	55
28	Progress on and challenges of p-type formation for GaN power devices. Journal of Applied Physics, 2020, 128, .	2.5	54
29	High-Quality AlN by Initial Layer-by-Layer Growth on Surface-Controlled 4H-SiC(0001) Substrate. Japanese Journal of Applied Physics, 2003, 42, L445-L447.	1.5	52
30	Accurate measurements of second-order nonlinear optical coefficients of 6H and 4H silicon carbide. Journal of the Optical Society of America B: Optical Physics, 2009, 26, 1892.	2.1	48
31	4H-SiC BJTs With Record Current Gains of 257 on (0001) and 335 on ($\{000\}\text{-}\{1\}$). IEEE Electron Device Letters, 2011, 32, 841-843.	3.9	46
32	P-Channel MOSFETs on 4H-SiC {0001} and Nonbasal Faces Fabricated by Oxide Deposition and $\{N\}_2O$ Annealing. IEEE Transactions on Electron Devices, 2009, 56, 1953-1958.	3.0	45
33	Experimental and Theoretical Investigations on Short-Channel Effects in 4H-SiC MOSFETs. IEEE Transactions on Electron Devices, 2005, 52, 1954-1962.	3.0	41
34	4H-SiC Lateral Double RESURF MOSFETs With Low on Resistance. IEEE Transactions on Electron Devices, 2007, 54, 1216-1223.	3.0	40
35	1580-V μ s ⁻¹ 40- μ m ² Double-RESURF MOSFETs on 4H-SiC($\{000\}\text{-}\{1\}$). IEEE Electron Device Letters, 2009, 30, 831-833.	3.9	40
36	Temperature dependence of barrier height in Ni/n-GaN Schottky barrier diode. Applied Physics Express, 2017, 10, 051002.	2.4	40

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37	Quantitative comparison between $Z1\hat{\cdot}2$ center and carbon vacancy in 4H-SiC. Journal of Applied Physics, 2014, 115, .	2.5	39
38	Overview of carrier compensation in GaN layers grown by MOVPE: toward the application of vertical power devices. Japanese Journal of Applied Physics, 2020, 59, SA0804.	1.5	39
39	Growth of AlN $(11\hat{r}\{2\}0)$ on 6H-SiC $(11\hat{r}\{2\}0)$ by Molecular-Beam Epitaxy. Japanese Journal of Applied Physics, 2002, 41, L1348-L1350.	1.5	38
40	Defect evolution in Mg ions implanted GaN upon high temperature and ultrahigh N ₂ partial pressure annealing: Transmission electron microscopy analysis. Journal of Applied Physics, 2020, 127, .	2.5	38
41	High-quality nonpolar 4H-AlN grown on 4H-SiC (112 $\hat{\text{A}}$ 0) substrate by molecular-beam epitaxy. Applied Physics Letters, 2006, 89, 112117.	3.3	37
42	Deep-level transient spectroscopy studies of electron and hole traps in n-type GaN homoepitaxial layers grown by quartz-free hydride-vapor-phase epitaxy. Applied Physics Letters, 2019, 115, .	3.3	37
43	Breakdown Characteristics of 15-kV-Class 4H-SiC PiN Diodes With Various Junction Termination Structures. IEEE Transactions on Electron Devices, 2012, 59, 2748-2752.	3.0	36
44	Improvement of Channel Mobility in Inversion-Type n-Channel GaN Metal $\hat{\text{e}}$ “Oxide $\hat{\text{e}}$ “Semiconductor Field-Effect Transistor by High-Temperature Annealing. Japanese Journal of Applied Physics, 2008, 47, 7784.	1.5	35
45	Molecular-beam epitaxial growth of insulating AlN on surface-controlled 6H $\hat{\text{e}}$ “SiC substrate by HCl gas etching. Applied Physics Letters, 2002, 80, 76-78.	3.3	34
46	Ultrahigh-Voltage SiC MPS Diodes With Hybrid Unipolar/Bipolar Operation. IEEE Transactions on Electron Devices, 2017, 64, 874-881.	3.0	34
47	1330 V, 67 m/spl Omega//spl middot/cm/sup 2/ 4H-SiC(0001) RESURF MOSFET. IEEE Electron Device Letters, 2005, 26, 649-651.	3.9	33
48	Reduction of deep levels generated by ion implantation into n- and p-type 4H $\hat{\text{e}}$ “SiC. Journal of Applied Physics, 2010, 108, .	2.5	33
49	Deep levels induced by reactive ion etching in n- and p-type 4H $\hat{\text{e}}$ “SiC. Journal of Applied Physics, 2010, 108, 023706.	2.5	33
50	Improvement of Current Gain in 4H-SiC BJTs by Surface Passivation With Deposited Oxides Nitrided in $\$hbox{N}_{2}\$ or NO. IEEE Electron Device Letters, 2011, 32, 285-287.$	3.9	33
51	Control of carrier lifetime of thick n-type 4H-SiC epilayers by high-temperature Ar annealing. Applied Physics Express, 2016, 9, 061303.	2.4	33
52	Correlation between shapes of Shockley stacking faults and structures of basal plane dislocations in 4H-SiC epilayers. Philosophical Magazine, 2017, 97, 2736-2752.	1.6	33
53	Time-resolved nonlinear luminescence of biexcitons in ZnSe-ZnxMg1 $\hat{\sim}$ xSySe1 $\hat{\sim}$ y single quantum wells. Physical Review B, 1995, 52, R2289-R2292.	3.2	32
54	Promise and Challenges of High-Voltage SiC Bipolar Power Devices. Energies, 2016, 9, 908.	3.1	31

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55	Interface state density of SiO ₂ /p-type 4H-SiC (0001), (112 \hat{A}), (11 \hat{A} 00) metal-oxide-semiconductor structures characterized by low-temperature subthreshold slopes. Applied Physics Letters, 2016, 108, .	3.3	31
56	Identification of dislocations in 4H-SiC epitaxial layers and substrates using photoluminescence imaging. Japanese Journal of Applied Physics, 2014, 53, 020304.	1.5	30
57	Redistribution of Mg and H atoms in Mg-implanted GaN through ultra-high-pressure annealing. Applied Physics Express, 2020, 13, 086501.	2.4	30
58	Identification of origin of E_C \sim 0.6 eV electron trap level by correlation with iron concentration in n-type GaN grown on GaN freestanding substrate by metalorganic vapor phase epitaxy. Applied Physics Express, 2020, 13, 071007.	2.4	30
59	Improved Dielectric and Interface Properties of 4H-SiC MOS Structures Processed by Oxide Deposition and N ₂ &O Annealing. Materials Science Forum, 2006, 527-529, 987-990.	0.3	29
60	Reduction of Threading Dislocation Density in 2H-AlN Grown on 6H-SiC(0001) by Minimizing Unintentional Active-Nitrogen Exposure before Growth. Applied Physics Express, 2011, 4, 025502.	2.4	29
61	Enhancement of carrier lifetime in lightly Al-doped p-type 4H-SiC epitaxial layers by combination of thermal oxidation and hydrogen annealing. Applied Physics Express, 2014, 7, 085501.	2.4	28
62	Nonradiative recombination at threading dislocations in 4H-SiC epilayers studied by micro-photoluminescence mapping. Journal of Applied Physics, 2011, 110, .	2.5	27
63	Enhancement of Carrier Lifetimes in n-Type 4H-SiC Epitaxial Layers by Improved Surface Passivation. Applied Physics Express, 2010, 3, 121201.	2.4	26
64	Over-700-nm Critical Thickness of AlN Grown on 6H-SiC(0001) by Molecular Beam Epitaxy. Applied Physics Express, 2012, 5, 105502.	2.4	26
65	Hall scattering factors in p-type 4H-SiC with various doping concentrations. Applied Physics Express, 2016, 9, 041301.	2.4	26
66	Doping-Induced Lattice Mismatch and Misorientation in 4H-SiC Crystals. Materials Science Forum, 0, 717-720, 481-484.	0.3	25
67	4H-SiC pn Photodiodes with Temperature-Independent Photoresponse up to 300 $^{\circ}$ C. Applied Physics Express, 2012, 5, 094101.	2.4	25
68	Temperature Dependence of Impact Ionization Coefficients in 4H-SiC. Materials Science Forum, 0, 778-780, 461-466.	0.3	25
69	Accurate method for estimating hole trap concentration in n-type GaN via minority carrier transient spectroscopy. Applied Physics Express, 2018, 11, 071002.	2.4	25
70	Improvement of Carrier Lifetimes in Highly Al-Doped p-Type 4H-SiC Epitaxial Layers by Hydrogen Passivation. Applied Physics Express, 2013, 6, 121301.	2.4	24
71	Electrical properties of n- and p-type 4H-SiC formed by ion implantation into high-purity semi-insulating substrates. Japanese Journal of Applied Physics, 2017, 56, 070306.	1.5	24
72	Electric-field-induced simultaneous diffusion of Mg and H in Mg-doped GaN prepared using ultra-high-pressure annealing. Applied Physics Express, 2019, 12, 111005.	2.4	24

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73	Nitrogen-displacement-related electron traps in <i>n</i> -type GaN grown on a GaN freestanding substrate. Applied Physics Letters, 2021, 118, .	3.3	24
74	ZrB ₂ Substrate for Nitride Semiconductors. Japanese Journal of Applied Physics, 2003, 42, 2260-2264.	1.5	22
75	Shockley-Read-Hall lifetime in homoepitaxial p-GaN extracted from recombination current in GaN <i>n</i> ⁺ junction diodes. Japanese Journal of Applied Physics, 2019, 58, SCCB14.	1.5	22
76	Impact Ionization Coefficients in GaN Measured by Above- and Sub-E _g Illuminations for p ⁺ <i>n</i> ⁺ Junction. , 2019, , .		22
77	Effects of ultra-high-pressure annealing on characteristics of vacancies in Mg-implanted GaN studied using a monoenergetic positron beam. Scientific Reports, 2020, 10, 17349.	3.3	22
78	Accurate measurement of quadratic nonlinear-optical coefficients of gallium nitride. Journal of the Optical Society of America B: Optical Physics, 2010, 27, 2026.	2.1	21
79	Measurement of avalanche multiplication utilizing Franz-Keldysh effect in GaN p-n junction diodes with double-side-depleted shallow bevel termination. Applied Physics Letters, 2019, 115, .	3.3	21
80	Lattice relaxation process of AlN growth on atomically flat 6H-SiC substrate in molecular beam epitaxy. Journal of Crystal Growth, 2002, 237-239, 1012-1016.	1.5	20
81	Single-crystalline 4H-SiC micro cantilevers with a high quality factor. Sensors and Actuators A: Physical, 2013, 197, 122-125.	4.1	20
82	Temperature dependence of optical absorption coefficient of 4H- and 6H-SiC from room temperature to 300 Å°C. Japanese Journal of Applied Physics, 2014, 53, 108003.	1.5	20
83	Ion implantation technology in SiC for power device applications. , 2014, , .		20
84	Reduction of plasma-induced damage in n-type GaN by multistep-bias etching in inductively coupled plasma reactive ion etching. Applied Physics Express, 2020, 13, 016505.	2.4	20
85	Mg-implanted bevel edge termination structure for GaN power device applications. Applied Physics Letters, 2021, 118, .	3.3	20
86	Design and demonstration of nearly-ideal edge termination for GaN <i>n</i> junction using Mg-implanted field limiting rings. Applied Physics Express, 2021, 14, 074002.	2.4	19
87	4H-SiC MIS Capacitors and MISFETs With Deposited $\text{SiN}_x/\text{SiO}_2$ Stack-Gate Structures. IEEE Transactions on Electron Devices, 2008, 55, 2054-2060.	3.0	18
88	Deep levels generated by thermal oxidation in p-type 4H-SiC. Journal of Applied Physics, 2013, 113, .	2.5	18
89	Reduction of interface state density in SiC (0001) MOS structures by post-oxidation Ar annealing at high temperature. AIP Advances, 2017, 7, .	1.3	18
90	Franz-Keldysh effect in GaN p-n junction diode under high reverse bias voltage. Applied Physics Letters, 2018, 112, .	3.3	18

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91	Surface passivation on 4H-SiC epitaxial layers by SiO ₂ with POCl ₃ annealing. Applied Physics Express, 2016, 9, 051301.	2.4	17
92	Why do electron traps at $E_C - 0.6$ eV have inverse correlation with carbon concentrations in n-type GaN layers?. Japanese Journal of Applied Physics, 2020, 59, 105505.	1.5	17
93	Improvement of channel property of GaN vertical trench MOSFET by compensating nitrogen vacancies with nitrogen plasma treatment. Applied Physics Express, 2020, 13, 124003.	2.4	17
94	Enhanced activation of Mg ion-implanted GaN at decreasing annealing temperature by prolonging duration. Applied Physics Express, 2021, 14, 011005.	2.4	17
95	Effect of annealing time and pressure on electrical activation and surface morphology of Mg-implanted GaN annealed at 1300 Å°C in ultra-high-pressure nitrogen ambient. Applied Physics Express, 2021, 14, 121004.	2.4	17
96	Gas-Source Molecular Beam Epitaxial Growth of (Zn, Mg)(S, Se) Using Bis-methylcyclopentadienyl-magnesium and Hydrogen Sulfide. Japanese Journal of Applied Physics, 1994, 33, L290-L293.	1.5	16
97	Effects of 6H-SiC surface reconstruction on lattice relaxation of AlN buffer layers in molecular-beam epitaxial growth of GaN. Applied Physics Letters, 2002, 81, 5141-5143.	3.3	16
98	Quantum-confinement effect on holes in silicon nanowires: Relationship between wave function and band structure. Journal of Applied Physics, 2011, 109, 064318.	2.5	16
99	Thermo-Optic Coefficients of 4H-SiC, GaN, and AlN for Ultraviolet to Infrared Regions up to 500 Å°C. Japanese Journal of Applied Physics, 2012, 51, 112101.	1.5	16
100	Effect of ultrathin AlN spacer on electronic properties of GaN/SiC heterojunction bipolar transistors. Japanese Journal of Applied Physics, 2014, 53, 034101.	1.5	16
101	Optical Properties of ZnSe/ZnMgSSe Single Quantum Wells Grown by Metalorganic Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1994, 33, L986-L989.	1.5	15
102	Ultrahigh-Voltage (> 20 kV) SiC PiN Diodes with a Space-Modulated JTE and Lifetime Enhancement Process via Thermal Oxidation. Materials Science Forum, 0, 778-780, 832-835.	0.3	15
103	Enhancement of initial layer-by-layer growth and reduction of threading dislocation density by optimized Ga pre-irradiation in molecular-beam epitaxy of 2H-AlN on 6H-SiC(0001). Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2094-2096.	0.8	14
104	Breakdown characteristics of 20 kV-class 4H-SiC PiN diodes with improved junction termination structures. , 2012, , .		14
105	Deep Levels Generated by Thermal Oxidation in n-Type 4H-SiC. Applied Physics Express, 2013, 6, 051301.	2.4	14
106	Formation mechanism of threading-dislocation array in AlN layers grown on 6H-SiC (0001) substrates with 3-bilayer-high surface steps. Applied Physics Letters, 2014, 105, .	3.3	14
107	Impact of Film Stress of Field-Plate Dielectric on Electric Characteristics of GaN-HEMTs. IEEE Transactions on Electron Devices, 2020, 67, 5421-5426.	3.0	14
108	Isochronal annealing study of Mg-implanted p-type GaN activated by ultra-high-pressure annealing. Applied Physics Express, 2021, 14, 056501.	2.4	14

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109	Dependence of Electrical Characteristics on Epitaxial Layer Structure of AlGaIn/GaN HEMTs Fabricated on Freestanding GaN Substrates. IEEE Transactions on Electron Devices, 2022, 69, 88-95.	3.0	14
110	Sources of Epitaxial Growth-Induced Stacking Faults in 4H-SiC. Journal of Electronic Materials, 2010, 39, 1166-1169.	2.2	13
111	Formation of highly vertical trenches with rounded corners via inductively coupled plasma reactive ion etching for vertical GaN power devices. Applied Physics Letters, 2021, 118, .	3.3	13
112	Increase of reverse leakage current at homoepitaxial GaN p-n junctions induced by continuous forward current stress. Applied Physics Letters, 2021, 118, .	3.3	13
113	Scanning Capacitance and Spreading Resistance Microscopy of SiC Multiple-pn-Junction Structure. Japanese Journal of Applied Physics, 2002, 41, L40-L42.	1.5	12
114	Enhanced Drain Current of 4H-SiC MOSFETs by Adopting a Three-Dimensional Gate Structure. IEEE Transactions on Electron Devices, 2009, 56, 2632-2637.	3.0	12
115	Optical Properties of Highly Strained AlN Coherently Grown on 6H-SiC(0001). Applied Physics Express, 2013, 6, 062604.	2.4	12
116	Oxidation-induced majority and minority carrier traps in n- and p-type 4H-SiC. Applied Physics Express, 2015, 8, 111301.	2.4	12
117	Effects of the sequential implantation of Mg and N ions into GaN for p-type doping. Applied Physics Express, 2021, 14, 111001.	2.4	12
118	Thermo-Optic Coefficients of 4H-SiC, GaN, and AlN for Ultraviolet to Infrared Regions up to 500 Å°C. Japanese Journal of Applied Physics, 2012, 51, 112101.	1.5	12
119	Identification of type of threading dislocation causing reverse leakage in GaN p-n junctions after continuous forward current stress. Scientific Reports, 2022, 12, 1458.	3.3	12
120	Growth evolution of cubic-GaN on sapphire (0001) substrate by metalorganic molecular beam epitaxy. Journal of Crystal Growth, 1999, 201-202, 437-440.	1.5	11
121	Comprehensive analysis of multiple-reflection effects on rotational Maker-fringe experiments. Journal of the Optical Society of America B: Optical Physics, 2008, 25, 1616.	2.1	11
122	Defect Control in Growth and Processing of 4H-SiC for Power Device Applications. Materials Science Forum, 0, 645-648, 645-650.	0.3	11
123	Demonstration of Common-Emitter Operation in AlGaIn/SiC Heterojunction Bipolar Transistors. IEEE Electron Device Letters, 2010, 31, 942-944.	3.9	11
124	4H-SiC bipolar junction transistors with record current gains of 257 on (0001) and 335 on (0001)., 2011, .		11
125	Orientation and Shape Effects on Ballistic Transport Properties in Gate-All-Around Rectangular Germanium Nanowire nFETs. IEEE Transactions on Electron Devices, 2013, 60, 944-950.	3.0	11
126	Phonon-Limited Electron Mobility in Rectangular Cross-Sectional Ge Nanowires. IEEE Transactions on Electron Devices, 2014, 61, 1993-1998.	3.0	11

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127	4H-SiC MISFETs With 4H-AlN Gate Insulator Isopolytypically Grown on 4H-SiC $(11\bar{1}0)$. IEEE Electron Device Letters, 2014, 35, 339-341.	3.9	11
128	Interface properties of NO-annealed 4H-SiC (0001), $(112\bar{1})$, and $(11\bar{1}00)$ MOS structures with heavily doped p-bodies. Journal of Applied Physics, 2017, 121, .	2.5	11
129	Analysis of intrinsic reverse leakage current resulting from band-to-band tunneling in dislocation-free GaN μ n junctions. Applied Physics Express, 2021, 14, 114001.	2.4	11
130	SiO ₂ /GaN interfaces with low defect densities and high breakdown electric fields formed by plasma-enhanced atomic layer deposition. Japanese Journal of Applied Physics, 2022, 61, SC1073.	1.5	11
131	Mobility oscillation by one-dimensional quantum confinement in Si-nanowire metal-oxide-semiconductor field effect transistors. Journal of Applied Physics, 2009, 106, 034312.	2.5	10
132	High Channel Mobilities of MOSFETs on Highly-Doped 4H-SiC (11-20) Face by Oxidation in N ₂ /O ₂ Ambient. Materials Science Forum, 2004, 457-460, 1429-1432.	0.3	9
133	N ₂ O-grown oxides/4H-SiC (0001), $(033\bar{1}8)$, and $(112\bar{1})$ interface properties characterized by using p-type gate-controlled diodes. Applied Physics Letters, 2008, 93, .	3.3	9
134	Enhanced Channel Mobility in 4H-SiC MISFETs by Utilizing Deposited SiN/SiO ₂ Stack Gate Structures. Materials Science Forum, 2008, 600-603, 679-682.	0.3	9
135	Nonpolar 4H-AlN grown on 4H-SiC $(11\bar{1}00)$ with reduced stacking fault density realized by persistent layer-by-layer growth. Applied Physics Letters, 2008, 93, 082106.	3.3	9
136	Improved Performance of 4H-SiC Double Reduced Surface Field Metal-Oxide-Semiconductor Field-Effect Transistors by Increasing RESURF Doses. Applied Physics Express, 2008, 1, 101403.	2.4	9
137	Enhanced Current Gain (>250) in 4H-SiC Bipolar Junction Transistors by a Deep-Level-Reduction Process. Materials Science Forum, 2012, 717-720, 1117-1122.	0.3	9
138	Long Photoconductivity Decay Characteristics in p-Type 4H-SiC Bulk Crystals. Japanese Journal of Applied Physics, 2013, 52, 010202.	1.5	9
139	Effects of Parasitic Region in SiC Bipolar Junction Transistors on Forced Current Gain. Materials Science Forum, 2018, 924, 629-632.	0.3	9
140	Reliability of Nitrided Gate Oxides for N- and P-Type 4H-SiC(0001) Metal-Oxide-Semiconductor Devices. Japanese Journal of Applied Physics, 2011, 50, 090201.	1.5	9
141	Selective Area Growth of Cubic GaN on 3C-SiC (001) by Metalorganic Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2000, 39, L1081-L1083.	1.5	8
142	Systematic Investigation of c-Axis Tilt in GaN and AlGaN Grown on Vicinal SiC(0001) Substrates. Japanese Journal of Applied Physics, 2009, 48, 020202.	1.5	8
143	Nondestructive Visualization of Individual Dislocations in 4H-SiC Epilayers by Micro Photoluminescence Mapping. Japanese Journal of Applied Physics, 2010, 49, 090201.	1.5	8
144	Franz-Keldysh effect in n-type GaN Schottky barrier diode under high reverse bias voltage. Applied Physics Express, 2016, 9, 091002.	2.4	8

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145	Effects of Dosage Increase on Electrical Properties of Metal-Oxide-Semiconductor Diodes with Mg-Implanted GaN Before Activation Annealing. <i>Physica Status Solidi (B): Basic Research</i> , 2020, 257, 1900367.	1.5	8
146	Electron Injection from GaN to SiC and Fabrication of GaN/SiC Heterojunction Bipolar Transistors. <i>Materials Science Forum</i> , 2006, 527-529, 1545-1548.	0.3	7
147	Polytype Replication in Heteroepitaxial Growth of Nonpolar AlN on SiC. <i>MRS Bulletin</i> , 2009, 34, 348-352.	3.5	7
148	Temperature dependence of current gain in 4H-SiC bipolar junction transistors. <i>Japanese Journal of Applied Physics</i> , 2015, 54, 04DP13.	1.5	7
149	Strong impact of the initial III/V ratio on the crystalline quality of an AlN layer grown by rf-plasma-assisted molecular-beam epitaxy. <i>Applied Physics Express</i> , 2016, 9, 025502.	2.4	7
150	Design Criterion for SiC BJTs to Avoid ON-Characteristics Degradation Due to Base Spreading Resistance. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 2086-2091.	3.0	7
151	Phonon-assisted optical absorption due to Franz-Keldysh effect in 4H-SiC p-n junction diode under high reverse bias voltage. <i>Applied Physics Express</i> , 2018, 11, 091302.	2.4	7
152	Demonstration of Conductivity Modulation in SiC Bipolar Junction Transistors With Reduced Base Spreading Resistance. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 4870-4874.	3.0	7
153	Electron traps formed by gamma-ray irradiation in homoepitaxial n-type GaN and their annealing behavior. <i>AIP Advances</i> , 2020, 10, 045023.	1.3	7
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